

InGaN / GaN Blue Chip 203SB

Ver.6 (2006/01/11)

1. Scope

- The specification applies to InGaN LED chips.
- Type : 203 SB

2. Structure

- InGaN / GaN Blue LED chip.
- P Electrode (anode) : Gold
- N Electrode (cathode) : Gold

3. Size

- Chip size : 0.305 mm × 0.330 mm (12mil × 13mil).
- Pattern drawing : per fig.

4.ESD

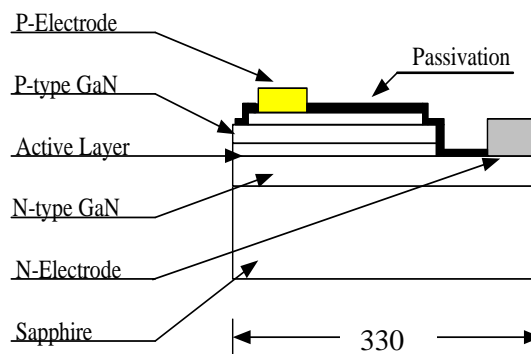
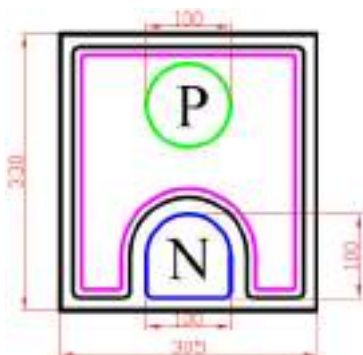
- HBM : -500 V

5. Electro-Optical Characteristics Electro-Optical Characteristics (Ta= +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$			3.6	V
Reverse Current	I_r	$V_r = 5 \text{ V}$			1	μA
Radiant intensity	I_v	$I_F = 20 \text{ mA}$	*	*	*	mcd
Wavelength	Hue	$I_F = 20 \text{ mA}$	455	460	480	nm
Spectrum Width of Half Value	$\Delta \lambda$	$I_F = 20 \text{ mA}$		30		nm

Specifications Explanation : P□□□—□

Intensity Specifications : P□XX—X	Wavelength Specifications : PX□X—X	Process Spec : PXX□—X	LOP Grade : PXXX—□
* 30 ≤ E < 40	450 ≤ G < 455	⊙P : With TCL Film	No.□:10mcd one Grade
* 40 ≤ F < 50	455 ≤ H < 460	⊙O : With ITO Film	
* 50 ≤ G < 60	460 ≤ I < 465	⊙H : With HB LED	
* 60 ≤ H < 70	465 ≤ J < 470		
* 70 ≤ I < 90	470 ≤ K < 475		
* 90 ≤ J < 120	475 ≤ L < 480		
* 120 ≤ K < 160			

 unit : μm

Chip-Thickness: 90 ± 10 μm